

March 2009

# FGH40N60SF 600V, 40A Field Stop IGBT

### **Features**

- · High current capability
- Low saturation voltage: V<sub>CE(sat)</sub> =2.3V @ I<sub>C</sub> = 40A
- · High input impedance
- Fast switching
- RoHS compliant

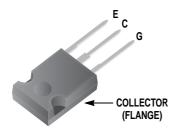
# **Applications**

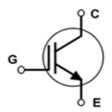
• Inverter, UPS, SMPS, PFC



### **General Description**

Using Novel Field Stop IGBT Technology, Fairchild's new sesries of Field Stop IGBTs offer the optimum performance for Inverter, UPS, SMPS and PFC applications where low conduction and switching losses are essential.





# **Absolute Maximum Ratings**

Symbol	Description		Ratings	Units	
V <sub>CES</sub>	Collector to Emitter Voltage		600	V	
V <sub>GES</sub>	Gate to Emitter Voltage		± 20	V	
I <sub>C</sub>	Collector Current	$@ T_C = 25^{\circ}C$	80	А	
	Collector Current	$@ T_C = 100^{\circ}C$	40	А	
I <sub>CM (1)</sub>	Pulsed Collector Current	$ T_C = 25^{\circ}C $	120	А	
$P_{D}$	Maximum Power Dissipation	$@ T_C = 25^{\circ}C$	290	W	
	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	116	W	
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units	
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.43	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W	

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# **Package Marking and Ordering Information**

			Packaging		Max Qty
<b>Device Marking</b>	Device	Package	Туре	Qty per Tube	per Box
FGH40N60SF	FGH40N60SFTU	TO-247	Tube	30ea	-

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250 \mu A$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250\mu A$	-	0.6	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	μΑ
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C} = 250 \mu A, V_{CE} = V_{GE}$	4.0	5.0	6.5	V
OL(III)		I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V	-	2.3	2.9	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C	-	2.5	-	V
Dynamic C	haracteristics			•		
C <sub>ies</sub>	Input Capacitance		-	2110	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ f = 1MHz	-	200	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 - 11VII 12	-	60	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	25	-	ns
t <sub>r</sub>	Rise Time		-	42	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 40A,$	-	115	-	ns
t <sub>f</sub>	Fall Time	$R_G = 10\Omega$ , $V_{GE} = 15V$ ,	-	27	54	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	1.13	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.31	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	1.44	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	24	-	ns
t <sub>r</sub>	Rise Time		-	43	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 40A,$	-	120	-	ns
t <sub>f</sub>	Fall Time	$R_G = 10\Omega$ , $V_{GE} = 15V$ , Inductive Load, $T_C = 125^{\circ}C$	-	30	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	1.14	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.48	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	1.62	-	mJ
Qg	Total Gate Charge		-	120	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 400V, I_{C} = 40A,$ $V_{GF} = 15V$	-	14	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	*GE = 10 *	-	58	-	nC

Figure 1. Typical Output Characteristics

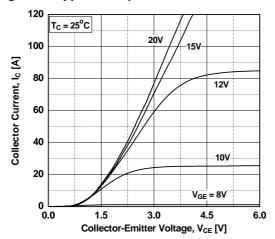


Figure 3. Typical Saturation Voltage Characteristics

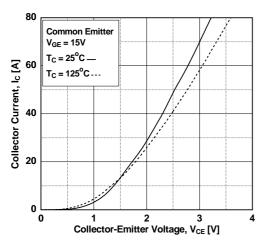
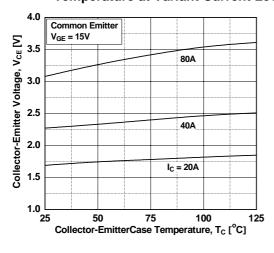
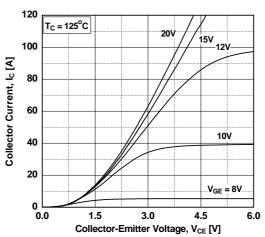


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 



**Figure 4. Transfer Characteristics** 

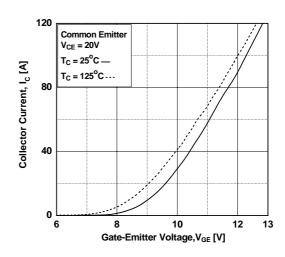


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

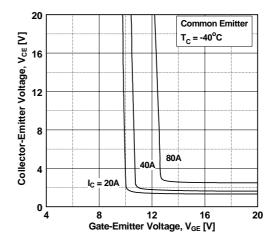


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

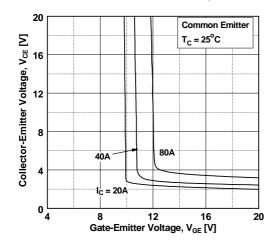


Figure 9. Capacitance Characteristics

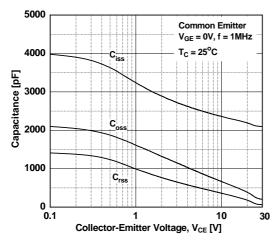


Figure 11. SOA Characteristics

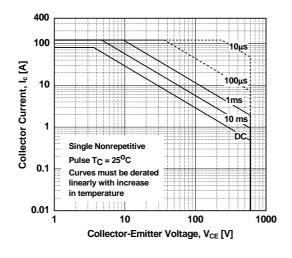


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

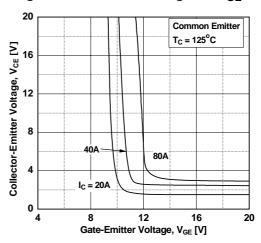


Figure 10. Gate charge Characteristics

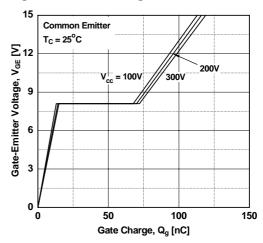


Figure 12. Turn-on Characteristics vs. Gate Resistance

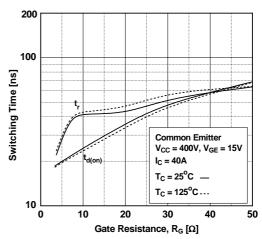


Figure 13. Turn-off Characteristics vs.
Gate Resistance

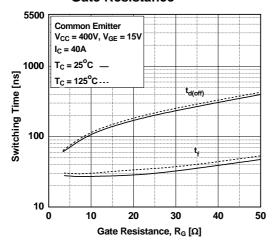


Figure 15. Turn-off Characteristics vs. Collector Current

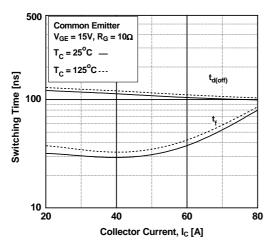


Figure 17. Switching Loss vs. Collector Current

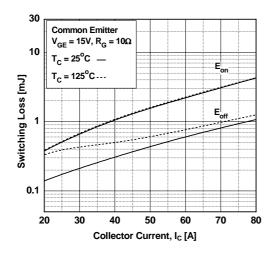


Figure 14. Turn-on Characteristics vs.
Collector Current

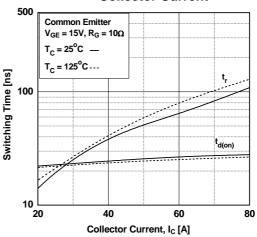


Figure 16. Switching Loss vs. Gate Resistance

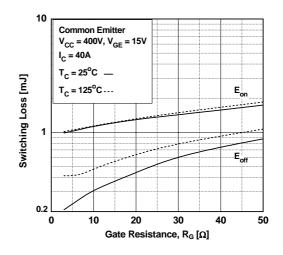
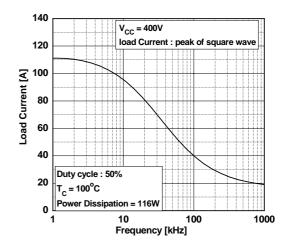


Figure 18. Load Current vs. Frequency



# Figure 19.Turn off Switching SOA Characteristics

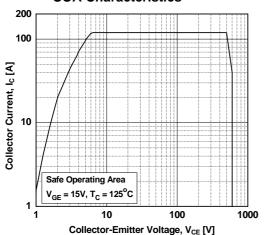
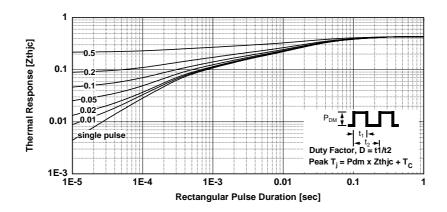
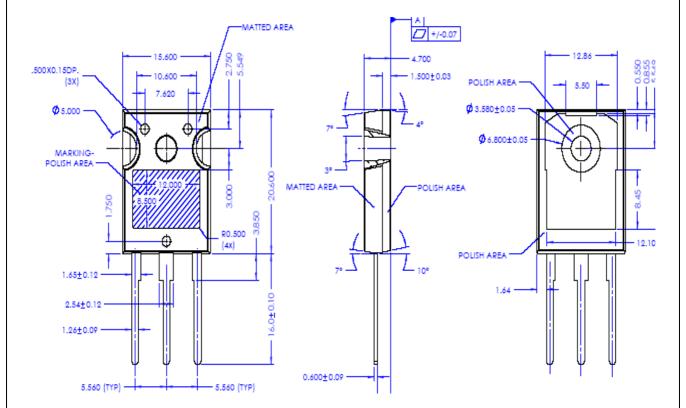


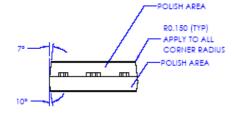
Figure 20. Transient Thermal Impedance of IGBT



# **Mechanical Dimensions**

# TO-247AB (FKS PKG CODE 001)





Dimensions in Millimeters



# U<sub>s</sub>

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